

Eff Improvement

MOSFET

Low $R_{DS(on)}$ for high D

Low gate charge for low D

Paralleling for high current

Schottky

Low forward drop

short recovery time

Lower gate drive V .

Inductor

Multiple parallel winding

CAPS

Low ESR

Parallel caps

Lower Inductor Ripple

Reduce RMS Loss
(inductor and output C)

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